User's Guide

1



Using the TPS40090EVM-002

User's Guide

EVM IMPORTANT NOTICE

Texas Instruments (TI) provides the enclosed product(s) under the following conditions:

This evaluation kit being sold by TI is intended for use for **ENGINEERING DEVELOPMENT OR EVALUATION PURPOSES ONLY** and is not considered by TI to be fit for commercial use. As such, the goods being provided may not be complete in terms of required design-, marketing-, and/or manufacturing-related protective considerations, including product safety measures typically found in the end product incorporating the goods. As a prototype, this product does not fall within the scope of the European Union directive on electromagnetic compatibility and therefore may not meet the technical requirements of the directive.

Should this evaluation kit not meet the specifications indicated in the EVM User's Guide, the kit may be returned within 30 days from the date of delivery for a full refund. THE FOREGOING WARRANTY IS THE EXCLUSIVE WARRANTY MADE BY SELLER TO BUYER AND IS IN LIEU OF ALL OTHER WARRANTIES, EXPRESSED, IMPLIED, OR STATUTORY, INCLUDING ANY WARRANTY OF MERCHANTABILITY OR FITNESS FOR ANY PARTICULAR PURPOSE.

The user assumes all responsibility and liability for proper and safe handling of the goods. Further, the user indemnifies TI from all claims arising from the handling or use of the goods. Please be aware that the products received may not be regulatory compliant or agency certified (FCC, UL, CE, etc.). Due to the open construction of the product, it is the user's responsibility to take any and all appropriate precautions with regard to electrostatic discharge.

EXCEPT TO THE EXTENT OF THE INDEMNITY SET FORTH ABOVE, NEITHER PARTY SHALL BE LIABLE TO THE OTHER FOR ANY INDIRECT, SPECIAL, INCIDENTAL, OR CONSEQUENTIAL DAMAGES.

TI currently deals with a variety of customers for products, and therefore our arrangement with the user **is not exclusive**.

TI assumes no liability for applications assistance, customer product design, software performance, or infringement of patents or services described herein.

Please read the EVM User's Guide and, specifically, the EVM Warnings and Restrictions notice in the EVM User's Guide prior to handling the product. This notice contains important safety information about temperatures and voltages. For further safety concerns, please contact the TI application engineer.

Persons handling the product must have electronics training and observe good laboratory practice standards.

No license is granted under any patent right or other intellectual property right of TI covering or relating to any machine, process, or combination in which such TI products or services might be or are used.

Mailing Address:

Texas Instruments Post Office Box 655303 Dallas, Texas 75265

Copyright © 2003, Texas Instruments Incorporated

DYNAMIC WARNINGS AND RESTRICTIONS

It is important to operate this EVM within the input voltage range of 0 Vdc to100 Vdc.

Exceeding the specified input range may cause unexpected operation and/or irreversible damage to the EVM. If there are questions concerning the input range, please contact a TI field representative prior to connecting the input power.

Applying loads outside of the specified output range may result in unintended operation and/or possible permanent damage to the EVM. Please consult the EVM User's Guide prior to connecting any load to the EVM output. If there is uncertainty as to the load specification, please contact a TI field representative.

During normal operation, some circuit components may have case temperatures greater than 50°C. The EVM is designed to operate properly with certain components above 50°C as long as the input and output ranges are maintained. These components include but are not limited to linear regulators, switching transistors, pass transistors, and current sense resistors. These types of devices can be identified using the EVM schematic located in the EVM User's Guide. When placing measurement probes near these devices during operation, please be aware that these devices may be very warm to the touch.

Mailing Address:

Texas Instruments Post Office Box 655303 Dallas, Texas 75265

Copyright © 2004, Texas Instruments Incorporated

TPS40090 Multi-Phase Buck Converter and TPS2834 Drivers Steps-Down from 12-V to 1.5-V at 100 A

Systems Power

Contents

1	Introduction	. 4
2	Features	. 5
3	Schematic	. 5
4	Component Selection	. 7
5	Test Setup	14
6	Test Results/Performance Data	15
7	Layout Considerations	19
8	EVM Assembly Drawing and PCB Layout	20
9	List of Materials	24

1 Introduction

The TPS40090EVM–002 multi-phase dc-to-dc converter utilizes the TPS40090 multi-phase controller and TPS2834 adaptive driver to step down a 12-V input to 1.5-V at 420 kHz. The output current can exceed 100 A. The TPS40090 provides fixed-frequency, peak current-mode control with forced-phase current balancing. Phase currents are sensed by the voltage drop across the DC resistance (DCR) of inductors. Other features include a single voltage operation, true differential output voltage sense, user programmable current limit, capacitor-programmable soft-start and a power good indicator. Device operation is specified in the TPS40090 datasheet^[1].

TPS40090EVM-002 can be configured into 2-, 3– or 4-phase operation. For 2-phase operation, populate R65 and R66 to tie PWM2 and PWM4 up to internal 5-V and leave components in related phases unpopulated. For 3-phase operation, tie PWM4 to BP5 through R66 only. For 4-phase operation, leave both R65 and R66 unpopulated.

In this user's guide, all the tests are conducted under 4 phase operation.



2 Features

PARAMETER	TEST CONDITIONS	MIN	TYP	МАХ	UNITS	
Input voltage range		10.5	12.0	14.0		
Output voltage set point		1.477	1.508	1.540	V	
Output current range	V _{IN} = 12 V	0	100	120	А	
Line regulation ⁽¹⁾	I_{OUT} rising from 10 A to 100 A, 10.5 V \leq V _{IN} \leq 14 V		±0.1%			
Load regulation	IOUT rising from 10 A to 100 A		±0.3%			
Load transient response voltage	IOUT rising from 10 A to 100 A		-160		mVPK	
change	IOUT falling from 100 A to 10 A		200			
Load transient response recovery	IOUT rising from 10 A to 100 A		< 10			
time	IOUT falling from 100 A to 10 A		< 15		μs	
Loop bandwidth	I _{OUT} = 100 A, I _{OUT} = 10 A		89		kHz	
Phase margin	I _{OUT} = 100 A		40		0	
Input ripple voltage			80	200	mVpv	
Output ripple voltage			15	25		
Output rise time					ms	
Operating frequency		370	418	454	kHz	
Full load efficiency	V _{IN} = 12 V, V _{OUT} = 1.5 V, I _{OUT} = 100 A		84.3%			
Current sharing tolerance	V _{IN} = 12 V, V _{OUT} = 1.5 V, I _{OUT} = 100 A		±5%	±10%		

Table 1. TPS40090EVM-002 Performance Summary

3 Schematic

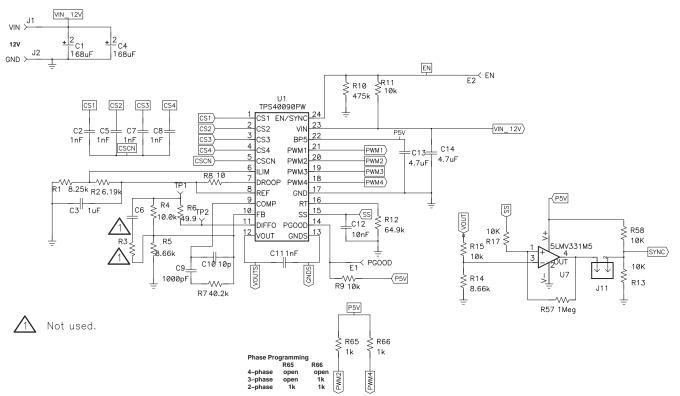


Figure 1. TPS40090EVM–002 Schematic Part 1 – TPS40090 Controller and Pre-Bias Circuit

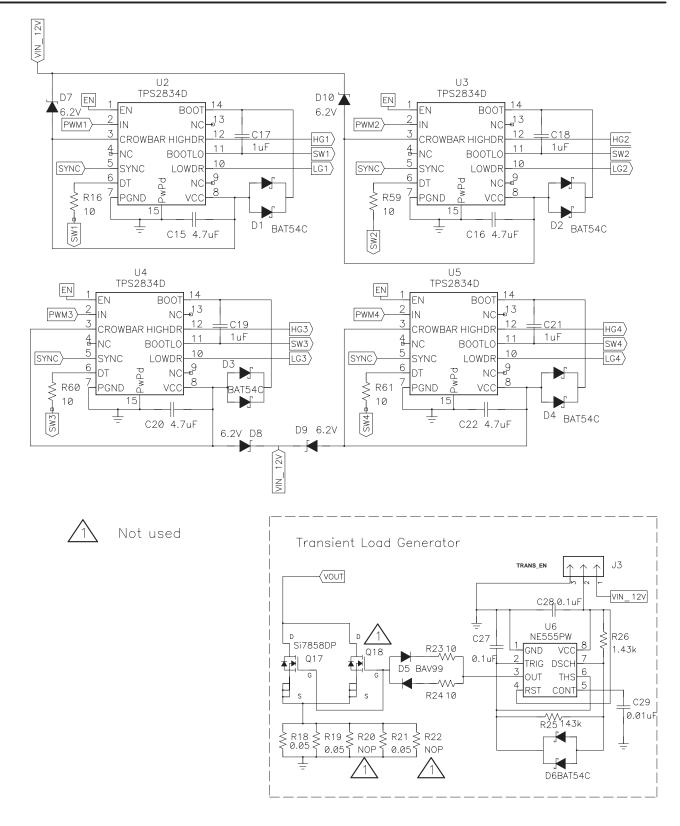


Figure 2. TPS40090EVM–002 Schematic Part 2 – Driver Circuit and Load Transient Generator

TEXAS INSTRUMENTS

 $\langle VIN_12V \rangle$

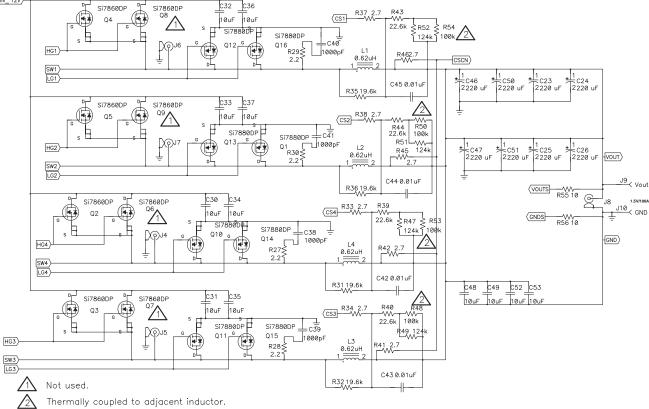


Figure 3. TPS40090EVM-002 Schematic Part 3 - Power Stage

4 Component Selection

4.1 Frequency of Operation

The clock oscillator frequency for the TPS40090 is programmed with a single resistor from RT (pin 16) to signal ground. Equation (1) from the datasheet allows selection of the R_T resistor in $k\Omega$ for a given switching frequency in kHz.

$$R_{T} = R12 = K_{PH} \times \left(39.2 \times 10^{3} \times f_{PH}^{-1.024} - 7\right) (k\Omega)$$
(1)

where

- K_{PH} is the coefficient that depends on the number of active phases
- *f*_{PH} is the single phase frequency, in kHz
- for 2-phase and 3-phase configurations K_{PH}=1.333
- for 4-phase K_{PH}=1.0 is a single phase frequency, kHz.

The R_T resistor value is returned by the last expression in k Ω . For 420 kHz, R_T is calculated as 65.8 k Ω and a resistor with a 64.9-k Ω standard value is used.

4.2 Inductance Value

The output inductor value for each phase can be calculated from the volt-second during off time, shown in equation (2).

$$L = \frac{V_{OUT}}{f \times I_{RIPPLE}} \times \left(1 - \frac{V_{OUT}}{V_{IN(max)}}\right)$$
(2)

where

• IRIPPLE is usually chosen to be between 10% and 40% of maximum phase current IPH(max).

With $I_{RIPPLE} = 20\%$ of $I_{PH(max)}$, there is a ripple current of 5 A, and the inductance value is found to be 0.63 μ H. Using SPM12550–R62M300 inductors from TDK, each had inductance of 0.6 μ H and resistance of 1.75-m Ω .

In multi-phase high current buck converter design, due to the ripple cancellation factor from interleaving, the inductor value could be smaller than that in a single phase operation. But from conduction loss point of view, the inductor value tends to be big to reduce the ripple current, thus losses.

4.3 Input Capacitor Selection

The bulk input capacitor selection is based on the input voltage ripple requirements. Due to the interleaving of multi phase, the input RMS current is reduced. The input ripple current RMS value over load current is calculated in equation (3).

$$\Delta I_{\rm IN(nom)} \left(N_{\rm PH}, \ D \right) =$$
(3)

$$\left[\left(D - \frac{k\left(N_{PH}, D\right)}{N_{PH}} \right) \times \left(\frac{k\left(N_{PH}, D\right) + 1}{N_{PH}} - D \right) \right] + \left(\frac{N_{PH}}{12 \times D^2} \right) \times \left[\frac{V_{OUT} \times (1 - D)}{L \times f \times (I_{OUT})} \right]^2 \times \left[\left(k\left(N_{PH}, D\right) + 1 \right)^2 \times \left(D - \frac{k\left(N_{PH}, D\right)}{N_{PH}} \right)^3 + k\left(N_{PH}, D\right)^2 \times \left(\frac{k\left(N_{PH}, D\right) + 1}{N_{PH}} - D \right)^3 \right] \right]$$

where

- $k(N_{PH}, D) = floor(N_{PH} \times D)$
- floor(x) is the function to return the greatest integer less than $N_{PH} \times D$
- N_{PH} is the number of active phases

Figure 4 shows the input ripple current RMS value over the load current versus duty cycle with different number of active phases.

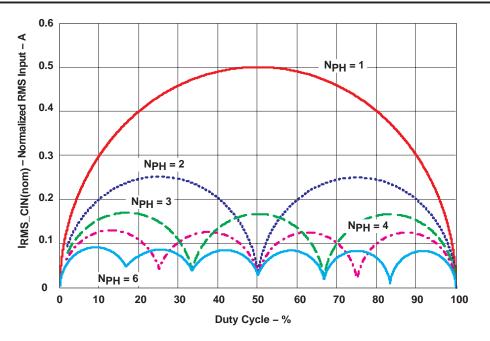


Figure 4. Input Ripple Current RMS Value Overload Current

The maximum input ripple RMS current can be estimated as shown in (4).

$$I \cong I_{OUT} \times \Delta I_{IN(nom)} (4, D_{min}) = 3.18 \text{ A}$$
(4)

It is also important to consider a minimum capacitance value which limits the voltage ripple to a specified value if all the current is supplied by the onboard capacitor. For a typical ripple voltage of 150 mV the maximum ESR is calculated in (5) as:

$$\mathsf{ESR} = \frac{\Delta \,\mathsf{V}}{\Delta \,\mathsf{I}} = \frac{150\,\mathsf{mV}}{3.18\,\mathsf{A}} = 47\,\mathsf{m}\Omega\tag{5}$$

Two 68- μ F, 20-V Oscon capacitors (20SVP68M) from Sanyo are placed on the input side of the board. The ESR is 40 m Ω for each capacitor.

4.4 Output Ripple Cancellation and Capacitor Selection

Due to the interleaving of channels, the total output ripple current is smaller than the ripple current from a single phase. The ripple cancellation factor is expressed in equation (6).

$$\Delta I_{OUT} \left(N_{PH}, D \right) = \frac{\begin{pmatrix} N_{PH} \\ i = 1 \end{pmatrix} |i - N_{PH} \times D|}{\begin{bmatrix} N_{PH}^{-1} \\ \Pi \\ i = 1 \end{pmatrix} (|i - N_{PH} \times D| + 1)}$$
(6)

$$k(N_{PH}, D) = if(N_{PH} \le 1, \Delta I_{OUT}(D), \Delta I_{OUT}(N_{PH}, D))$$

where

- D is the duty cycle for a single phase
- N_{PH} is the number of active phases
- K (N_{PH}) is the intermediate function for calculation

In this case, N_{PH}=4 and D_{min}=0.107 which yields k=0.573.

The actual output ripple is calculated in equation (7)

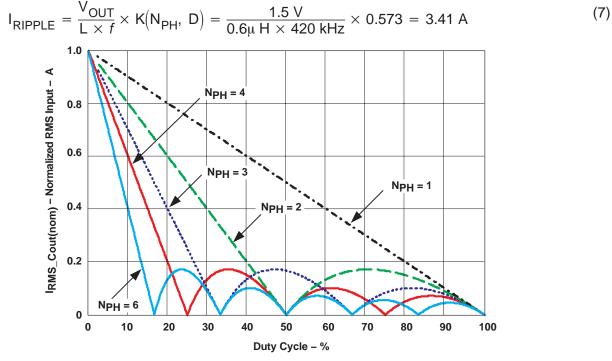


Figure 5. Output Ripple Current Cancellation

Selection of the output capacitor is based on many application variables, including function, cost, size, and availability. There are three ways to calculate the output capacitance.

1. The minimum allowable output capacitance is determined by the amount of inductor ripple current and the allowable output ripple, as given in equation (8).

$$C_{OUT(min)} = \frac{I_{RIPPLE}}{8 \times f \times V_{RIPPLE}} = \frac{3.41 \text{ A}}{8 \times 420 \text{ kHz} \times 10 \text{ mV}} = 101 \text{ }\mu\text{F}$$
(8)

In this design, $C_{OUT(min)}$ is 101-µF with V_{RIPPLE} =10 mV. However, this affects only the capacitive component of the ripple voltage, and the final value of capacitance is generally influenced by ESR and transient considerations.

2. ESR limitation. (To limit the ripple voltage to 10 mV, the capacitor ESR should be less than the value calculated in equation (9)).

$$R_{C} < = \frac{V_{RIPPLE}}{I_{RIPPLE}} = \frac{10 \text{ mV}}{3.41 \text{ A}} = 2.93 \text{ m}\Omega$$
(9)

3. Transient consideration. An additional consideration in the selection of the output inductor and capacitance value can be derived from examining the transient voltage overshoot which can be initiated with a load step from full load to no load. By equating the inductive energy with the capacitive energy the equation (10) can be derived.

$$C_{OUT} = \frac{L \times I^2}{V^2} = \frac{L_{EQ} \times \left(\left(I_{OH} \right)^2 - \left(I_{OL} \right)^2 \right)}{\left(V_{OUT2} \right)^2 - \left(V_{OUT1} \right)^2} = \frac{\frac{0.6 \mu H}{4} \times (100 \text{ A})^2}{\left((1.75 \text{ V})^2 - (1.5 \text{ V})^2 \right)} = 1846 \,\mu\text{F}$$
(10)

where

- I_{OH} is full load
- I_{OL} is no load
- V_{OUT2} is the the allowed transient voltage rise
- V_{OUT1} is the initial voltage

In this 100-A design the capacitance required for limiting the transient is significantly larger than the capacitance required to keep the ripple acceptably low. Eight 220- μ F POSCAP capacitors are in parallel with four 22- μ F ceramic capacitors. The ESR of each POSCAP is 15m Ω .

4.5 MOSFET Selection

There are different requirements for switching FET(s) and rectifier FET(s) in the high-ratio step down application. The duty cycle is around 12%. So the rectifier FET(s) is on for most of the cycle. The conduction loss is dominant. Low- $R_{DS(on)}$ FET(s) are preferred. Also due to the dV/dt turn on of the rectifier FET(s) and cross conduction, choose a rectifier FET with Qgs > Qgd. When the switch node is falling, the Qgd can pull the gate of the lower FET below GND, which upsets the driver. Two Si7880DP from Siliconix are in parallel for the rectifier FET. The $R_{DS(on)}$ of this FET is 3 m Ω and Qgs=18nC, and Qgd=10.5nC.

The switching FET switches at high voltage and high current, the switching loss is dominant. One single Si7860DP is selected for its low total gate charge.

Both types of FET(s) are offered in the Powerpak SO–8 package.

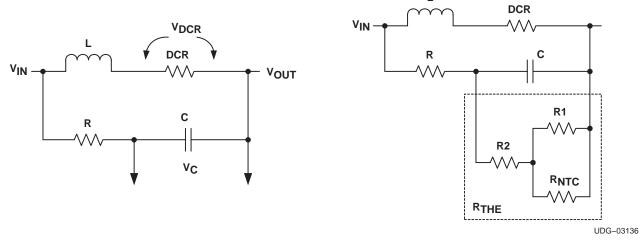
The PCB is layed out for two FETs in parallel, for both switching FET(s) and rectifier FET(s), to give the feasibility to modify the board for different applications.

4.6 Current Sensing

TPS40090 supports both resistor current sensing and DCR current sensing approach. DCRs of the output inductors are used in this design as the current sensing components. The DCR current sensing circuit is shown in Figure 5. The idea is to parallel a R-C network to the inductor. If the two time constants are same (L/DCR=R × C), then $V_C=V_{DCR}$. Extra circuit, shown in (b), is used to compensate the positive temperature coefficient of copper specific resistance, which is 0.385%/°C. See detail explanation in the datasheet.

With the chosen inductor described in *Inductance Value*, (section 4.2, of this document) the following values are used.

- R=19.6 kΩ
- C=10 nF
- R_{NTC}=100 kΩ
- R1=124 kΩ
- R2=22.6 kΩ



L

Figure 6. DCR Current Sensing Circuit with Copper Temperature Compensation

4.7 Overcurrent Limit Protection

The overcurrent function monitors the voltage level separately on each current sense input and compares it to the voltage on ILIM pin set by the divider from the controller's reference.

If the threshold of $V_{ILIM}/2.7$ is exceeded, the PWM cycle on the respected phase is terminated. Voltage level on the ILIM pin is determined by (11).

$$V_{\text{ILIM}} = 2.7 \times I_{\text{PH(max)}} \times R_{\text{CS}}; \quad I_{\text{PH(max)}} = I_{\text{OUT}} + \frac{\left(V_{\text{IN}} - V_{\text{OUT}}\right) \times V_{\text{OUT}}}{2 \times L_{\text{OUT}} \times f_{\text{SW}} \times V_{\text{IN}}}$$
(11)

where

- IPH(max) is the maximum allowable value of the phase current
- R_{CS} is the value of the current sense resistor



4.8 Compensation Components

The TPS40090 uses peak current mode control. Type II network is used here, which is implemented to provide one zero and two poles. The first pole is placed at the origin to improve DC regulation.

The ESR zero of the power stage is:

$$f_{\text{ESRZ}} = \frac{1}{2\pi \times R_{\text{C}} \times C_{\text{OUT}}} = 354 \text{ kHz}$$
(12)

The zero is placed near 3.96 kHz to produce a reasonable time constant.

$$f_{\rm Z} = \frac{1}{2\pi \times R7 \times C9} \tag{13}$$

The second pole is placed at ESR zero (354 kHz).

$$f_{\mathsf{P1}} = \frac{1}{2\pi \times \mathsf{R7} \times \left(\frac{(\mathsf{C9} \times \mathsf{C10})}{(\mathsf{C9} + \mathsf{C10})}\right)} \tag{14}$$

The resulting values selected for this design are:

• C9 = 1000 pF



UDG-04063

5 Test Setup

The HPA072 has the following input/output connections: 12-V input J1 (VIN) and J2 (GND), 1.5-V output J9 (VOUT) and J10 (GND). A diagram showing the connection points is shown in Figure 5. A power supply capable of supplying 18 A should be connected to VIN and GND through a pair of 10 AWG wires. The 1.5-V load should be connected respectively to J9 and J10 through pairs of 0 AWG wires. Wire lengths should be minimized to reduce losses in the wires. A 5-inch fan with 200-cfm air flow is recommended to operate this board at full load.

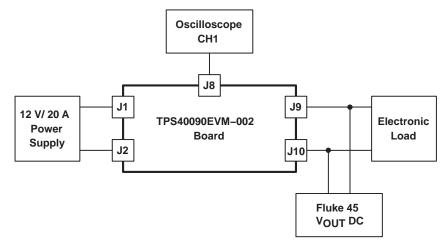


Figure 7. Connections for the Test

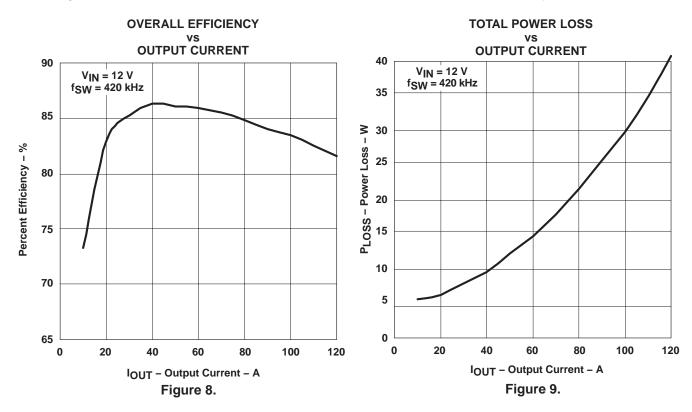


6 Test Results and Performance Data

6.1 Efficiency and Power Loss

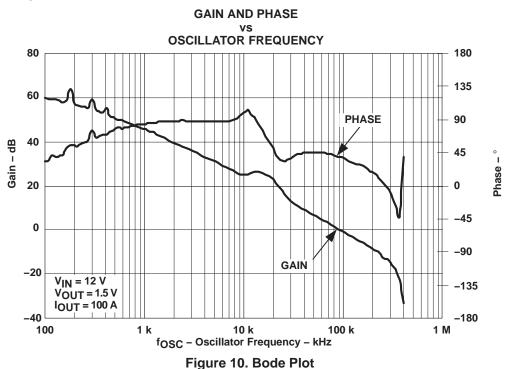
Figure 8 shows the efficiency as the load varies from 10 A to over 100 A. The efficiency at full load is about 84.3%.

Figure 7 shows the total loss versus the load current, which is approximately 28.3W at 100 A.



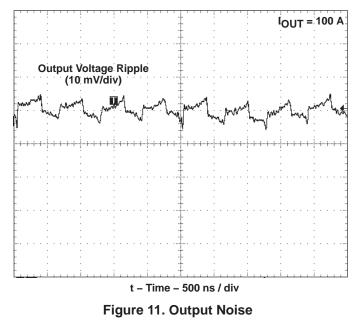
6.2 Closed-Loop Performance

The TPS40090 uses peak current-mode control. Figure 10 shows the bode plots at 100 A of load current, where no droop function is implemented. The crossover frequency is at 89 kHz with phase margin of 40°.



6.3 Output Ripple and Noise

Figure 11 shows typical output noise where V_{IN} =12 V, and I_{OUT} =100A. The output ripple is less than 10 mV.



6.4 Transient Response

The on-board load transient circuit enables to check the step load transient response on the same board. Simply by putting a jumper to connect Pin1 and 2 of J3, a 90-A step load is created by three 50-m Ω resistors placed on the board. The slew rates of the transient are 200 A/µs for the load step-down and 160 A/µs for the load step-up.

The transient response is shown in Figure 6 as the load is stepped from 10 to 100 A. The output deviation is approximately 200 mV and the settling time is within 15 μ s.

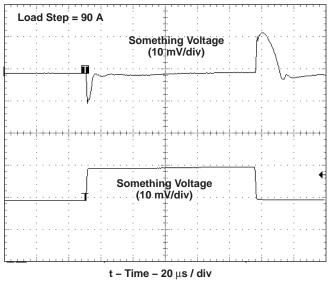


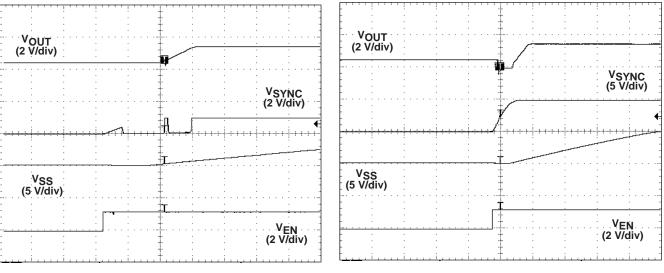
Figure 12. Transient Response



6.5 Start up with Pre-Biased Output

In synchronous buck converter, the bottom FET discharges the pre-biased output during start-up. To avoid this, a comparator U9 and surround components are used to pull the SYNC pin of the drivers low, which keeps the bottom FET off during startup. So the output can rise smoothly. After the SS pin comes up, SYNC is pulled up high and enable the bottom FET's driving signal. The converter goes back to normal synchronization mode. This function can be enabled by shorting J11 on the board.

Figure 8 shows the start-up waveform with pre-biased output with J11 short and open respectively. In Figure 12, there are two glitches of SYNC waveform. The first one is cause by P5V from TPS40090. When TPS40090 is enabled, P5V comes up first. SYNC is connected to P5V through a divider. The second one happens when the driver is ready and turns on the bottom FET when PWM signal is low. So the pre-biased output is pulled low which causes the SYNC signal high to turn off the bottom FET. Then output voltage goes back and rises up smoothly.



t – Time – 1 ms / div Figure 13. J11 Short Circuit

t – Time – 2.5 ms / div

Figure 14. J11 Open Circuit

7 Layout Considerations

The PCB layout plays a critical role in the performance in a high frequency switching power supply design. Following the suggestions listed below will help to improve the performance and expedite the design.

- To take full advantage of the ripple cancellation factor from interleaving, place the input capacitors before the junction where the input voltage is distributed to each phase. Place the output capacitors after the junction where all the inductors are connected;
- Place the external drivers right next to the FETs and use at least 25 mil trace for gate drive signal to improve noise immunity
- Place some ceramic capacitors in the input of each channel to filter the current spikes
- Place the NTC resistor right next to its related inductor for better thermal coupling
- 2 oz. or thicker copper is recommended to reduce the trace impedance
- Place enough vias along pads of the power components to increase thermal conduction
- Keep the current sensing traces as short as possible to avoid excessive noise pick up
- Place the output inductors as symmetric as possible in relation to the output connectors to obtain similar voltage drop from the trace impedance

8 EVM Assembly Drawing and PCB Layout

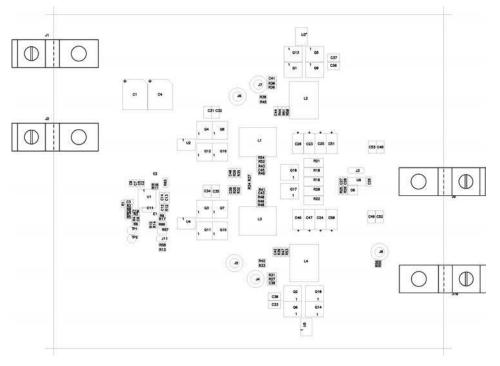


Figure 15. Top Side Component Assembly

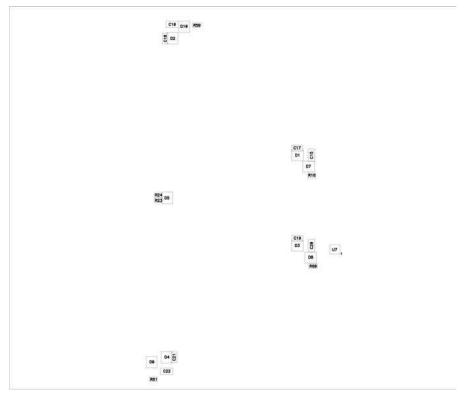
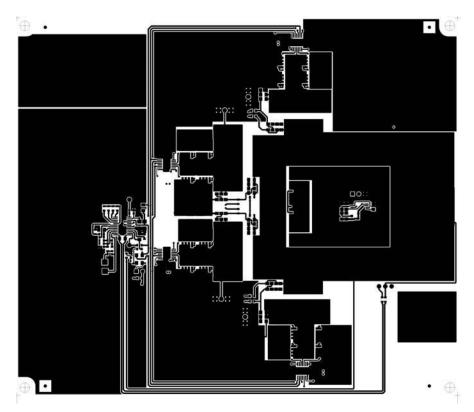


Figure 16. Bottom Assembly







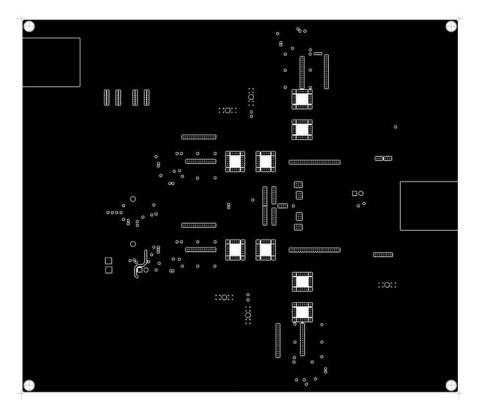


Figure 18. Internal 1 (Ground Plane)

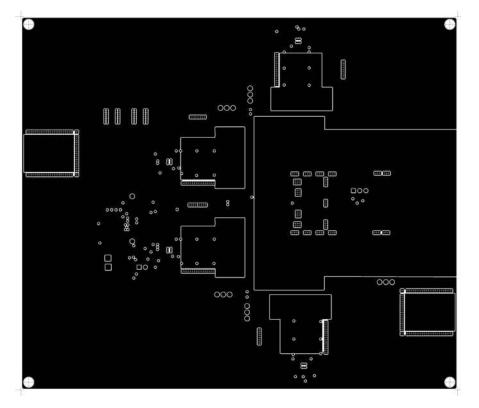


Figure 19. Internal 2 (Power Plane)

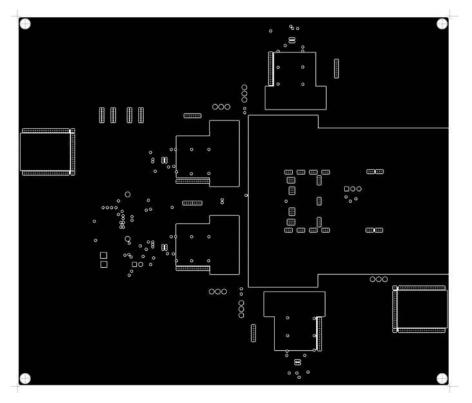


Figure 20. Internal 3

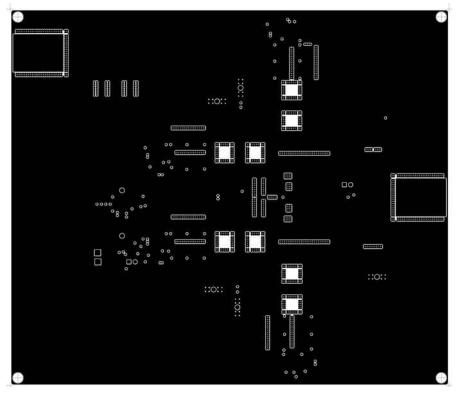


Figure 21. Internal 4

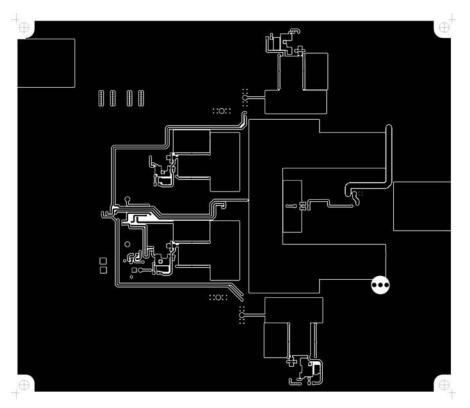


Figure 22. Bottom Layer Copper

9 List of Materials

The following table lists the TPS40090EVM–002 components corresponding to the schematic shown in Figure 1.

Reference Designator	QTY	Description	Size	Manufacturer	Part Number
C1, C4	2	Capacitor, OS–CON, 68 μF , 20 V, 40 m Ω , 20%	10.3mm (F8)	Sanyo	20SVP68M
C2, C5, C7, C8,C9, C11	6	Capacitor, ceramic, 1000-pF, 25 V, X7R, ±5%	603	muRata	GRM39SL102J25
C3,C17, C18, C19, C21	5	Capacitor, dielectric, 1.0 $\mu\text{F},~16$ V, $~\text{X7R},\pm10\%$	805	muRata	GRM40B105K16
C6	0		603	Std	Std
C10	1	Capacitor, ceramic, 10 pF, 50 V, COG, +2.5%	603	muRata	GRQ706COG100C50
C12	1	Capacitor, ceramic, 0.01 $\mu\text{F},~50$ V, X7R, $\pm5\%$	805	muRata	GRM40UJ103J50
C13, C14, C15, C16, C20, C22	6	Capacitor, dielectric, 4.7 $\mu\text{F},~16$ V, X5R, $~\pm10\%$	1206	muRata	GRM42– 65X5R475K16
C30, C31, C32, C33, C34, C35, C36, C37	8	Capacitor, dielectric, 10 μ F, 25 V, X5R	1210	TDK	C3225X5R1E106M
C38, C39, C40, C41	4	Capacitor, ceramic, 1000-pF, 50 V, X7R, ±5%	805	muRata	GRM40TH102J50
C42, C43, C44, C45	4	Capacitor, ceramic, 0.01 µF, 50 V, COG	805	TDK	C2012COG1H103JT
C23, C24, C25, C26,C46, C47,C50, C51	8	Capacitor, POSCAP, 220 $\mu\text{F},$ 2.5 V, 15 m $\Omega,$ 20%	7343 (D)	Sanyo	2R5TPE220M
C48, C49, C52, C53	4	Capacitor, Ceramic, 10 $\mu\text{F},~6.3$ V, X5R	1206	TDK	C3216X5R0J106M
D1, D2, D3, D4, D6	5	Diode, dual schottky, 200 mA, 30 V	SOT-23	Vishay-Liteon	BAT54C
D7, D8, D9, D10	4	Diode, zener, 6.2 V, 350 mW	SOT-23	Diodes, Inc.	BZX84C6V2
J1, J2, J9, J10	1	Lug, Solderless, #2 – #8 AWG, 1/4	Copper	524600	ILSCO
J4, J5, J6, J7, J8	5	Connector, shielded, test jack, vertical	0.0125 DIA	Johnson Components	129–0701–202
L1, L2, L3, L4	4	Inductor, SMT, 0.62 μ H, 30 A, 1.75 m Ω	0.524 x 0.492	TDK	SPM12550-R62M300
Q2, Q3, Q4, Q5	4	MOSFET, N-channel, 30 V, 18 A, 8.0 m Ω	PWRPAK S0-8	Vishay-Siliconix	Si7860DP
Q6, Q7, Q8, Q9	0	MOSFET, N-channel, 30 V, 18 A, 8.0 m Ω	PWRPAK S0–8	Vishay-Siliconix	Si7860DP
Q1, Q10, Q11, Q12, Q13, Q14, Q15, Q16	8	MOSFET, N-channel, 30 V, 29 A, 3 m Ω	PWRPAK S0-8	Vishay–Siliconix	Si7880DP
R1	1	Resistor, chip, 8.25 kΩ, 1/16–W, 1%	603	Std	Std
R2	1	Resistor, chip, 6.19 kΩ,, 1/16–W, 1%	603	Std	Std
R3	0		603	Std	Std
R4, R9, R11	3	Resistor, chip, 10 k Ω , 1/16–W, 1%	603	Std	Std
R5	1	Resistor, chip, 8.66 kΩ, 1/16–W, 1%	603	Std	Std
R6	1	Resistor, chip, 49.9 Ω, 1/16–W, 1%	603	Std	Std
R7	1	Resistor, chip, 40.2 kΩ, 1/16–W, 1%	603	Std	Std
R8, R16, R55, R56, R59, R60, R61	7	Resistor, chip, 10–Ohms, 1/16–W, 1%	603	Std	Std
R10	1	Resistor, chip, 475 kΩ, 1/16–W, 5%	603	Std	Std
R12	1	Resistor, chip, 64.9 kΩ, 1/16–W, 1%	603	Std	Std

Table 2. List of Materials

Reference Designator	QTY	Description	Size	Manufacturer	Part Number
R27, R28, R29, R30	4	Resistor, chip, 2.2 Ω, 1/10–W, 1%	805	Std	Std
R31, R32,R35, R36	4	Resistor, chip, 19.6 kΩ, 1/10–W, 1%	805	Std	Std
R33, R34, R37, R38, R41, R42, R45, R46	8	Resistor, chip, 2.7 Ω , 1/16–W, 1%	603	Std	Std
R39, R40, R43, R44	4	Resistor, chip, 22.6 kΩ, 1/10–W, 1%	805	Std	Std
R47, R49, R51, R52	4	Resistor, chip, 124 kΩ, 1/10–W, 1%	805	Std	Std
R48, R50, R53, R54	4	NTC Resistor, chip, 100 kΩ, 1/10-W, 1%	805	Vishay	NTHS0603N01N1003 J
R65, R66	2	Resistor, chip, 1.0 kΩ, 1/10-W, 1%	805	Std	Std
TP1	1	Test point, 0.062 Hole, Red	0.25	Keystone	5011
TP2	1	Test point, 0.062 Hole, Black	0.25	Keystone	5010
U1	1	IC, high-frequency, multiphase controller	108,800	TI	TPS40090PW
U2, U3, U4, U5	4	IC, MOSFET driver, fast synchronous buck with DTC	PWP14	ТІ	TPS2834PWP
U6	1	IC, Precision timer	TSSOP 8	ТІ	NE555PW
E1, E2	2	Test point, black, 1 mm	0.038	Farnell	240-333
LOAD TRANSIE	NT CIR			1	
Q17	1	MOSFET, N-channel, 12 V, 29 A, 3.0 m Ω ,	PWRPAK S0-8		Si7858DP
Q18	0	MOSFET, N-channel, 12 V, 29 A, 3.0 mΩ,	PWRPAK S0–8		Si7858DP
R18, R19, R21	3	Resistor, chip, 0.050 Ω,, 1-W, 0.5%	2512	Vishay	WSL-2512-R050 0.5% R86
R20, R22	0	Resistor, chip, 0.050 Ω,, 1-W, 0.5%	2512	Vishay	WSL-2512-R050 0.5% R86
R23, R24	2	Resistor, chip, 10 Ω, 1/16–W, 1%	603	Std	Std
R25	1	Resistor, chip, 143 kΩ, 1/10–W, 1%	805	Std	Std
R26	1	Resistor, chip, 1.43 kΩ, 1/10–W, 1%	805	Std	Std
C27, C28	2	Capacitor, ceramic, 0.1 µF, 25 V, X7R, ±10%	805	TDK	C2012X7R1E104K
C29	1	Capacitor, ceramic, 0.01 µF, 50 V, X7R, ±5%	805	muRata	GRM40UJ103J50
D5	1	Diode, dual ultra fast, series, 200 mA, 70 V	SOT23	Fairchild	BAV99
D6	1	Diode, dual schottky, 200 mA, 30 V	SOT23	Vishay-Liteon	BAT54C
J3	1	Header, 3-pin, 100 mil spacing, (36-pin strip)	0.100 x 3	Sullins	PTC36SAAN
PRE-BIAS CIRC	UIT			L	
U7	1	IC, Single GP comparator, low voltage	SOT23-5	National	LMV331M5
J11	1	Header, 2-pin, 100 mil spacing, (36-pin strip)	0.100 x 2	Sullins	PTC36SAAN
R13, R15, R17, R58	4	Resistor, chip, 10 kΩ, 1/16–W, 1%	603	Std	Std
R57	1	Resistor, chip, 1 MΩ, 1/10–W, 1%	805	Std	Std
R14	1	Resistor, chip, 8.66 k Ω , 1/16–W, 1%	603	Std	Std

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products		Applications	
Amplifiers	amplifier.ti.com	Audio	www.ti.com/audio
Data Converters	dataconverter.ti.com	Automotive	www.ti.com/automotive
DSP	dsp.ti.com	Broadband	www.ti.com/broadband
Interface	interface.ti.com	Digital Control	www.ti.com/digitalcontrol
Logic	logic.ti.com	Military	www.ti.com/military
Power Mgmt	power.ti.com	Optical Networking	www.ti.com/opticalnetwork
Microcontrollers	microcontroller.ti.com	Security	www.ti.com/security
		Telephony	www.ti.com/telephony
		Video & Imaging	www.ti.com/video
		Wireless	www.ti.com/wireless

Mailing Address:

Texas Instruments

Post Office Box 655303 Dallas, Texas 75265

Copyright © 2005, Texas Instruments Incorporated